

BYC30MW-650PT2

Hyperfast power diode

Rev.03 - 22 May 2023

Product data sheet

1. General description

Hyperfast power diode in a 2-lead TO247 plastic package.



2. Features and benefits

- Excellent avalanche energy robustness
- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

	uick reference data						
Symbol	Parameter	Conditions	Notes	s Values			Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 109 °C; Fig. 1; Fig. 2; Fig. 3		30			A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 109 °C; square-wave pulse		60			A
I _{FSM} non-repetitive peak forward current		t_{p} = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>		270			A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297			А
Symbol	Parameter	Conditions	Notes	Min	Тур	Мах	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.05	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.38	1.80	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _i = 25 °C; Fig. 7		-	20	-	ns
					1		

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathod	С С С С С С С С С С С С С С С С С С С	

6. Ordering information

Table 3. Ordering information								
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BYC30MW-650PT2		BYC30MW-650PT2Q	Tube	30	TO247L-2L (L)	12-Nov-2020		
					TO247P-2L (P)	31-Mar-2023		

7. Marking

Table 4. Marking codes						
Type number	Marking codes					
	Assembly factory: L	Assembly factory: P				
BYC30MW-650PT2	BYC30MW 600PT2 PJLxxxx xx	BYC30MW 600PT2 PJPxxxx xx				

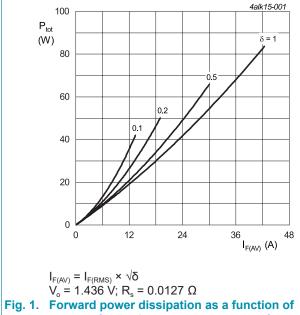
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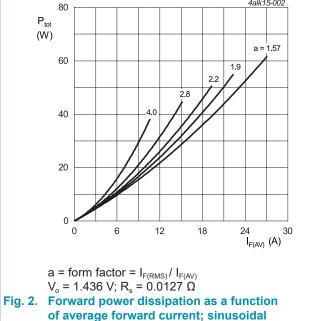
8. Limiting values

Table 5. Limiting values

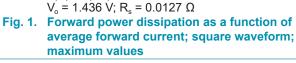
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V _{RRM}	repetitive peak reverse voltage			650	V
V _{RWM}	crest working reverse voltage			650	V
V _R	reverse voltage	DC		650	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 109 °C; Fig. 1; Fig. 2; Fig. 3		30	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 109 °C; square-wave pulse		60	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		270	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297	А
T _{stg}	storage temperature			-65 to 175	°C
Tj	junction temperature			-65 to 175	°C

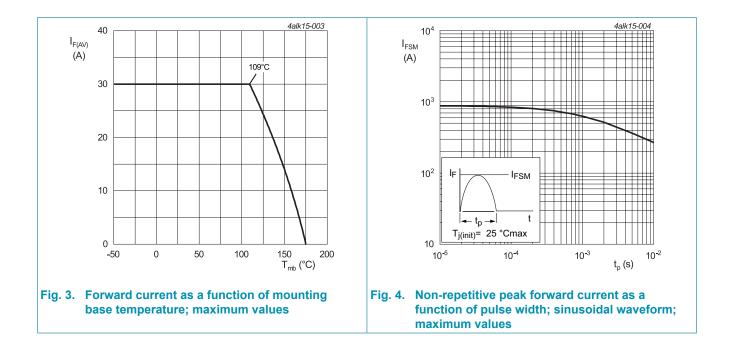




waveform; maximum values

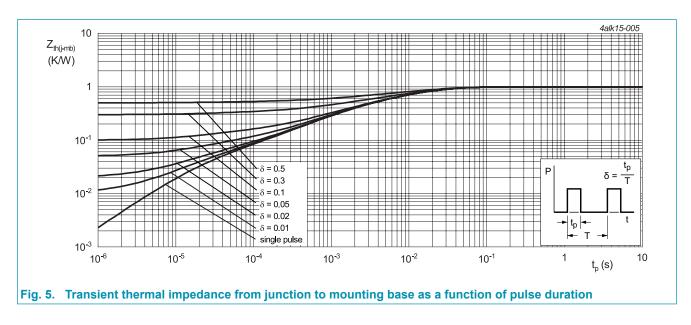


BYC30MW-650PT2 Hyperfast power diode



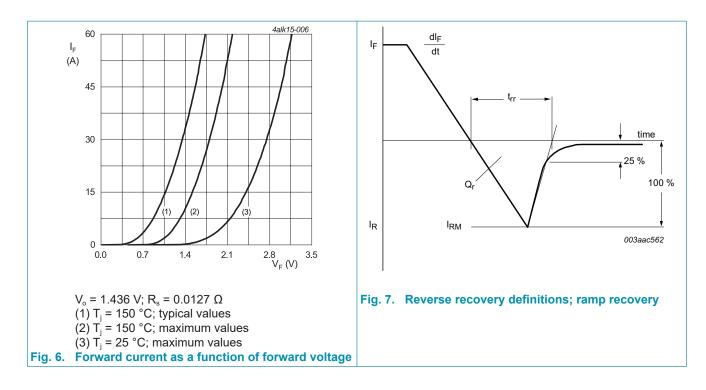
9. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	45	-	K/W



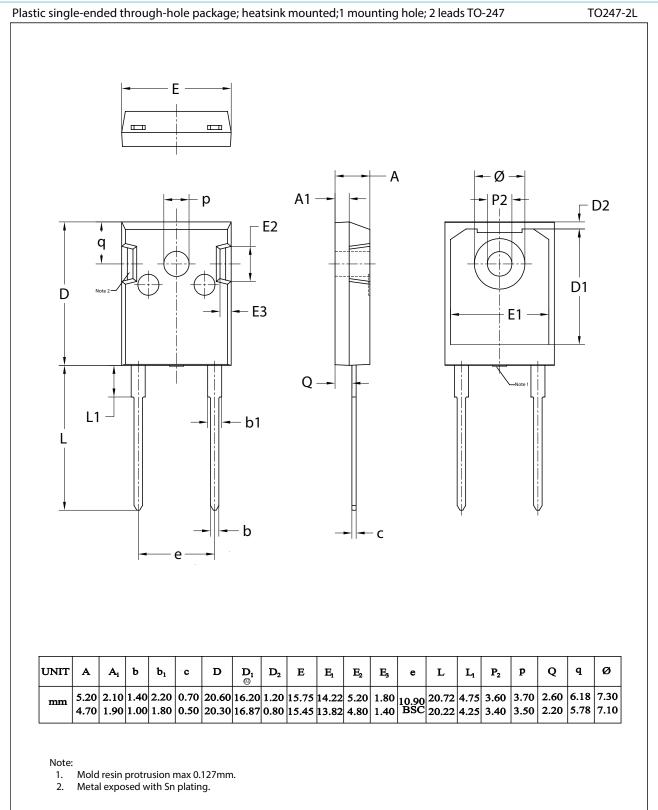
10. Characteristics

	naracteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.05	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.38	1.80	V
R	reverse current	V _R = 650 V; T _j = 25 °C		-	0.6	30	μA
		V _R = 650 V; T _j = 150 °C		-	0.25	1	mA
Dynamic	characteristics	1					
Q _r	reverse charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	68	-	nC
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>		-	330	-	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _j = 25 °C; <u>Fig. 7</u>		-	20	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	38	-	ns
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>		-	73	-	ns
I _{RM}	peak reverse recovery currentnon-repetitive	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	3.7	-	A
	avalanche energy	I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>		-	9.1	-	A
as	non-repetitive avalanche energy	T _{j(init)} = 25 °C		30	-	-	mJ

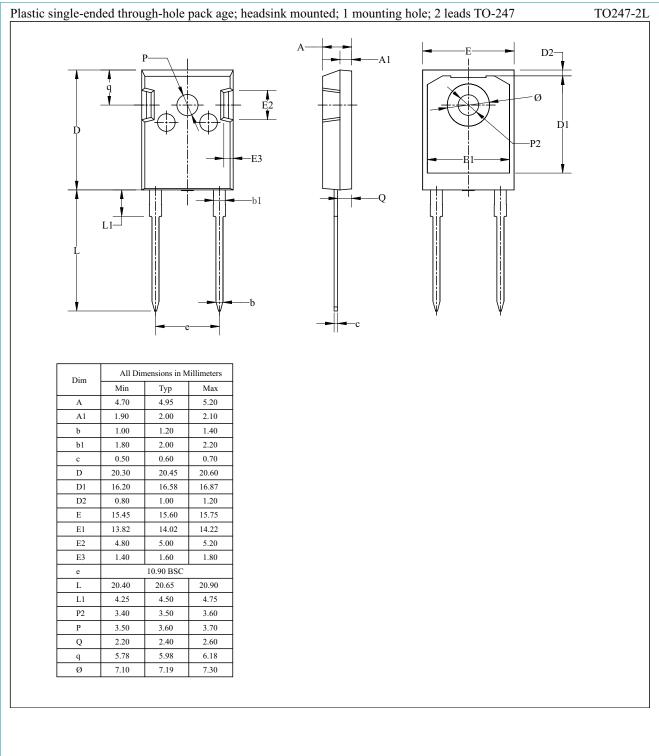


11. Package outline

Assembly factory: L



Assembly factory: P



BYC30MW-650PT2

Hyperfast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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